

# N-Channel 120 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
120	0.0029 at V <sub>GS</sub> = 10 V	188 <sup>a</sup>		

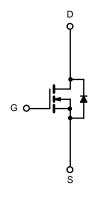
#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- New Package with Low Thermal Resistance
- 100 % R<sub>g</sub> Tested





Top View



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_{C} = 25 \text{ °C}$ , unless otherwise noted							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V <sub>DS</sub>	120	V				
Gate-Source Voltage	V <sub>GS</sub>	V <sub>GS</sub> ± 20					
Continuous Drain Current (T = $175 ^{\circ}$ C)	T <sub>C</sub> = 25 °C	1-	188 <sup>a</sup>				
Continuous Drain Current ( $T_J = 175 \text{ °C}$ )	T <sub>C</sub> = 125 °C	I <sub>D</sub>	143 <sup>a</sup>	A			
Pulsed Drain Current	I <sub>DM</sub>	650	A				
Avalanche Current	I <sub>AR</sub>	180					
Repetitive Avalanche Energy <sup>b</sup> L = 0.1 mH		E <sub>AR</sub>	2200	mJ			
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Р	398 <sup>c</sup>	w			
	T <sub>A</sub> = 25 °C	– P <sub>D</sub> –	5.9	vv			
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C				

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Limit	Unit			
Junction-to-Ambient	PCB Mount (TO-263) <sup>d</sup>	PCB Mount (TO-263) <sup>d</sup> R <sub>thJA</sub> 38					
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.4	°C/W				

Notes:

a. Package limited.

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b. Duty cycle ≤ 1 %.
c. See SOA curve for voltage derating.
d. When mounted on 1" square PCB (FR-4 material).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		•					
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS} = 0 V, I_{D} = 250 \mu A$	120				
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2		4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			50		
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	188			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0029	0.0040	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C			0.0053		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C			0.0065		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	68			S	
Dynamic <sup>b</sup>		•					
Input Capacitance	C <sub>iss</sub>			8150		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 60 V, f = 1 MHz		937			
Reverse Transfer Capacitance	C <sub>rss</sub>			110			
Total Gate Charge <sup>c</sup>	Qg			110	150	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 60 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		46			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			24			
Gate Resistance	R <sub>g</sub>		1.0		6.3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			22	33		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 60 \text{ V}, \text{ R}_{L} = 0.6 \Omega$		102	180		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 20$ Å, $V_{GEN}$ = 10 V, $R_g$ = 2.5 $\Omega$		53	85	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			18	35	1	
Source-Drain Diode Ratings and Cha	aracteristics	$\Gamma_{\rm C} = 25 \ {}^{\circ}{\rm C}^{\rm b}$					
Continuous Current	۱ <sub>S</sub>				188	^	
Pulsed Current	I <sub>SM</sub>				650	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			55	149	ns	
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>	I <sub>F</sub> = 20 A, dl/dt = 100 A/μs		5.3	10	А	
Reverse Recovery Charge	Q <sub>rr</sub>	1		0.15	0.37	μC	

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

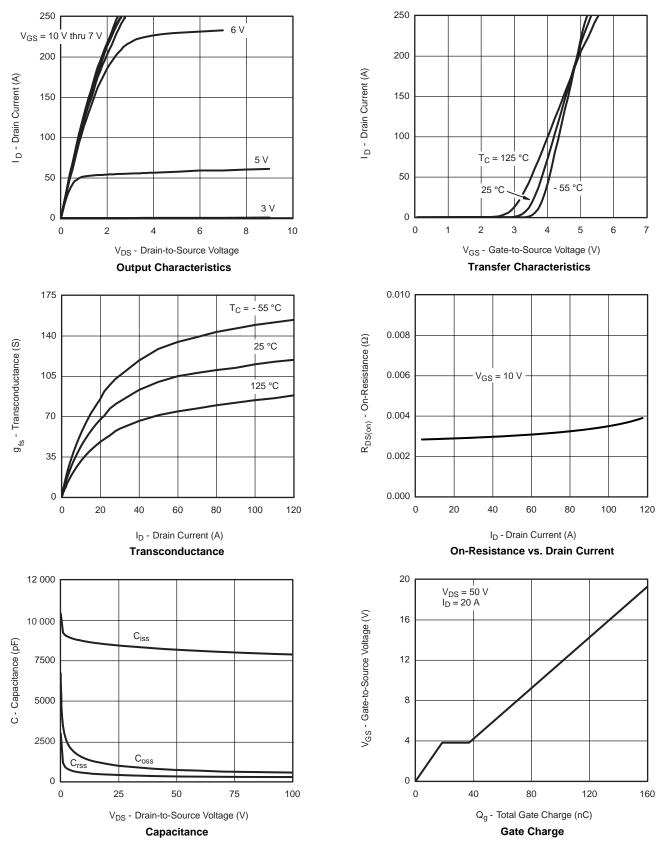
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

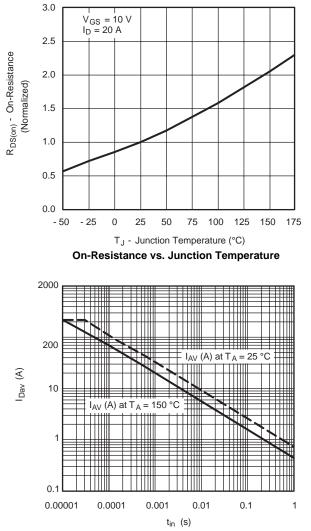




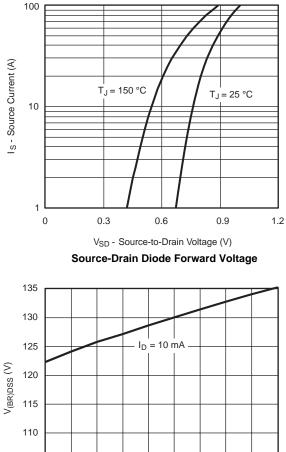


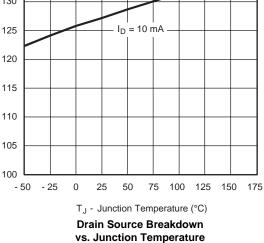
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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





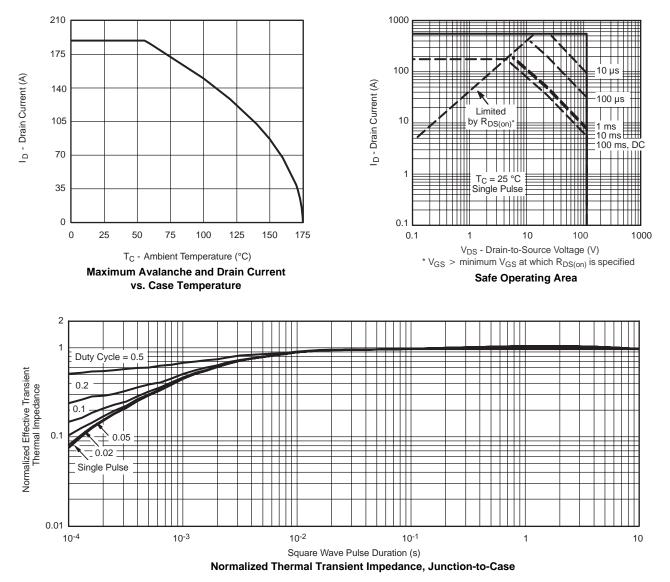






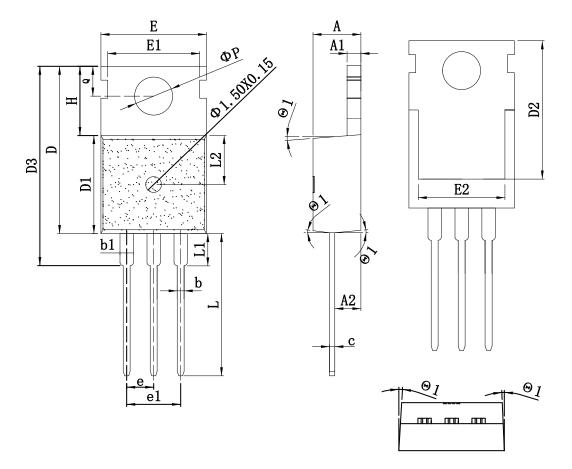
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#### **THERMAL RATINGS**





# TO-220\_3L-A PACKAGE OUTLINE

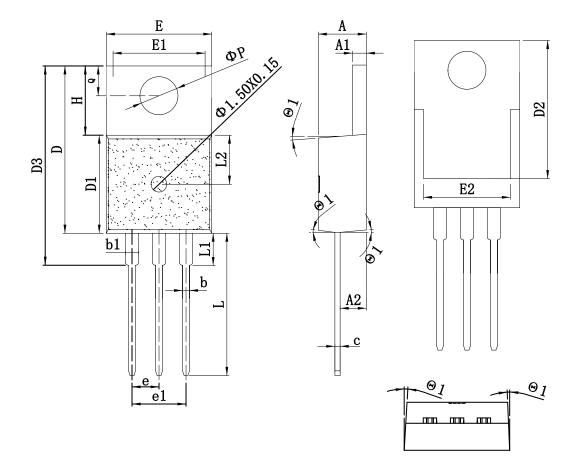


#### COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm		SYMBOL	mm			
SIMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
А	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
с	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



# TO-220\_3L-B PACKAGE OUTLINE



### COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm			
5 I WIDOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX	
А	4.15	4.50	4.80	E1	8.25	8.70	9.15	
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80	
A2	2.10	2.40	2.65	e	2.38	2.54	2.74	
b	0.65	0.80	1.00	e1	5.08REF			
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90	
с	0.35	0.50	0.65	L	12.75	13.28	13.70	
D	14.25	15.75	16.15	L1	-	-	3.50	
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00	
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85	
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00	
Е	8.68	10.02	11.00	θ	2°	-	7°	



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